



501.40922X00

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): N. HASEGAWA, et al

Serial No.: 09/996,762

Filed: November 30, 2001

For: FABRICATION METHOD OF SEMICONDUCTOR INTEGRATED
CIRCUIT DEVICE

Group: 2812

Examiner:

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

March 5, 2002

Sir:

The following preliminary amendments and remarks are respectfully submitted in connection with the above-identified application.

IN THE TITLE OF THE INVENTION:

Please amend the title of the invention as follows:

91 --METHOD OF FABRICATION OF SEMICONDUCTOR INTEGRATED
CIRCUIT DEVICE--.

IN THE SPECIFICATION:

Please replace the original specification with the attached Substitute Specification.

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TC 1700

IN THE ABSTRACT OF THE DISCLOSURE:

Please amend the abstract as follows:

ABSTRACT OF THE DISCLOSURE

az In order to shorten the time needed for fabricating semiconductor integrated circuit devices, a wafer is exposed while a chip area with defects of a mask is covered with a masking blade for light shielding.
